

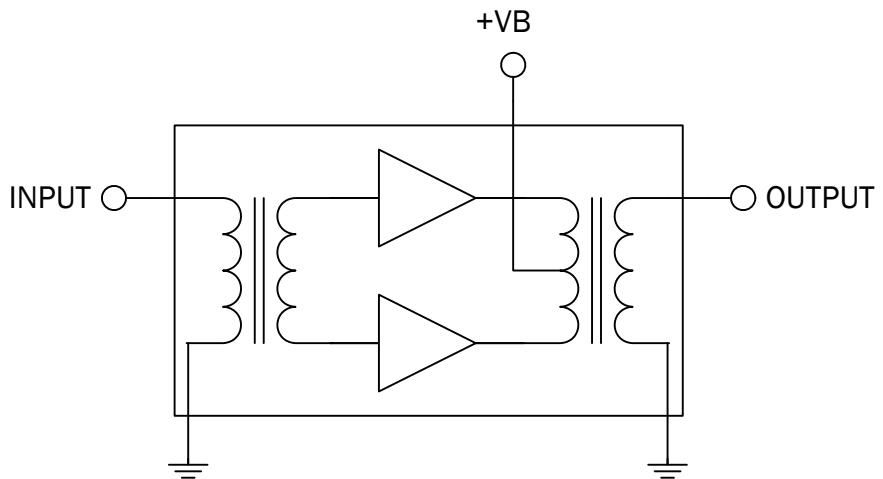


Package: SOT-115J



Features

- Excellent Linearity
- Superior Return Loss Performance
- Extremely Low Distortion
- Optimal Reliability
- Low Noise
- Unconditionally Stable Under All Terminations
- 28dB Min. Gain at 1003MHz
- 270mA Max. at 24V_{DC}



Functional Block Diagram

Applications

- 40MHz to 1003MHz CATV Amplifier Systems

Product Description

The RFPP2870 is a Hybrid Push Pull amplifier module. The part employs GaAs MESFET, GaAs pHEMT and GaN HEMT die and is operated from 40MHz to 1003MHz. It provides excellent linearity and superior return loss performance with low noise and optimal reliability.

Optimum Technology Matching® Applied

<input type="checkbox"/> GaAs HBT	<input type="checkbox"/> SiGe BiCMOS	<input checked="" type="checkbox"/> GaAs pHEMT	<input checked="" type="checkbox"/> GaN HEMT
<input checked="" type="checkbox"/> GaAs MESFET	<input type="checkbox"/> Si BiCMOS	<input type="checkbox"/> Si CMOS	<input type="checkbox"/> BiFET HBT
<input type="checkbox"/> InGaP HBT	<input type="checkbox"/> SiGe HBT	<input type="checkbox"/> Si BJT	<input type="checkbox"/> LDMOS

Absolute Maximum Ratings

Parameter	Rating	Unit
RF Input Voltage (single tone)	70	dBmV
DC Supply Over-Voltage (5 minutes)	30	V
Storage Temperature	-40 to +100	°C
Operating Mounting Base Temperature	-30 to +100	°C

**Caution!** ESD sensitive device.

Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical performance or functional operation of the device under Absolute Maximum Rating conditions is not implied.

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RoHS (Restriction of Hazardous Substances): Compliant per EU Directive 2002/95/EC.

Parameter	Specification			Unit	Condition
	Min.	Typ.	Max.		
Overall					$V_B = 24V; T_{MB} = 30^\circ C; Z_S = Z_L = 75\Omega$
Power Gain		27.0		dB	$f = 50MHz$
	28.0	28.5	29.0	dB	$f = 1003MHz$
Slope ^[1]	0.5	1.0	2.0	dB	$f = 40MHz$ to $1003MHz$
Flatness of Frequency Response			0.8	dB	$f = 40MHz$ to $1003MHz$ (Peak to Valley)
Input Return Loss	-20			dB	$f = 40MHz$ to $320MHz$
	-19			dB	$f = 320MHz$ to $640MHz$
	-18			dB	$f = 640MHz$ to $870MHz$
	-17			dB	$f = 870MHz$ to $1003MHz$
Output Return Loss	-20			dB	$f = 40MHz$ to $320MHz$
	-19			dB	$f = 320MHz$ to $640MHz$
	-18			dB	$f = 640MHz$ to $870MHz$
	-17			dB	$f = 870MHz$ to $1003MHz$
Noise Figure		4.5	5.0	dB	$f = 50MHz$ to $1003MHz$
Total Current Consumption (DC)		250.0	270.0	mA	
Distortion data 40MHz to 550MHz					$V_B = 24V; T_{MB} = 30^\circ C; Z_S = Z_L = 75\Omega$
CTB		-68		dBc	$V_O = 46dBmV$, flat, 79 analog channels plus 75 digital channels (-6dB offset)[2], [4]
XMOD		-64		dBc	
CSO		-75		dBc	
CIN		66		dB	
Distortion data 40MHz to 750MHz					$V_B = 24V; T_{MB} = 30^\circ C; Z_S = Z_L = 75\Omega$
Power Gain			-64		$V_O = 44dBmV$; 112 analog channels flat; [3], [4]
			-58		
Slope ^[1]			-65		

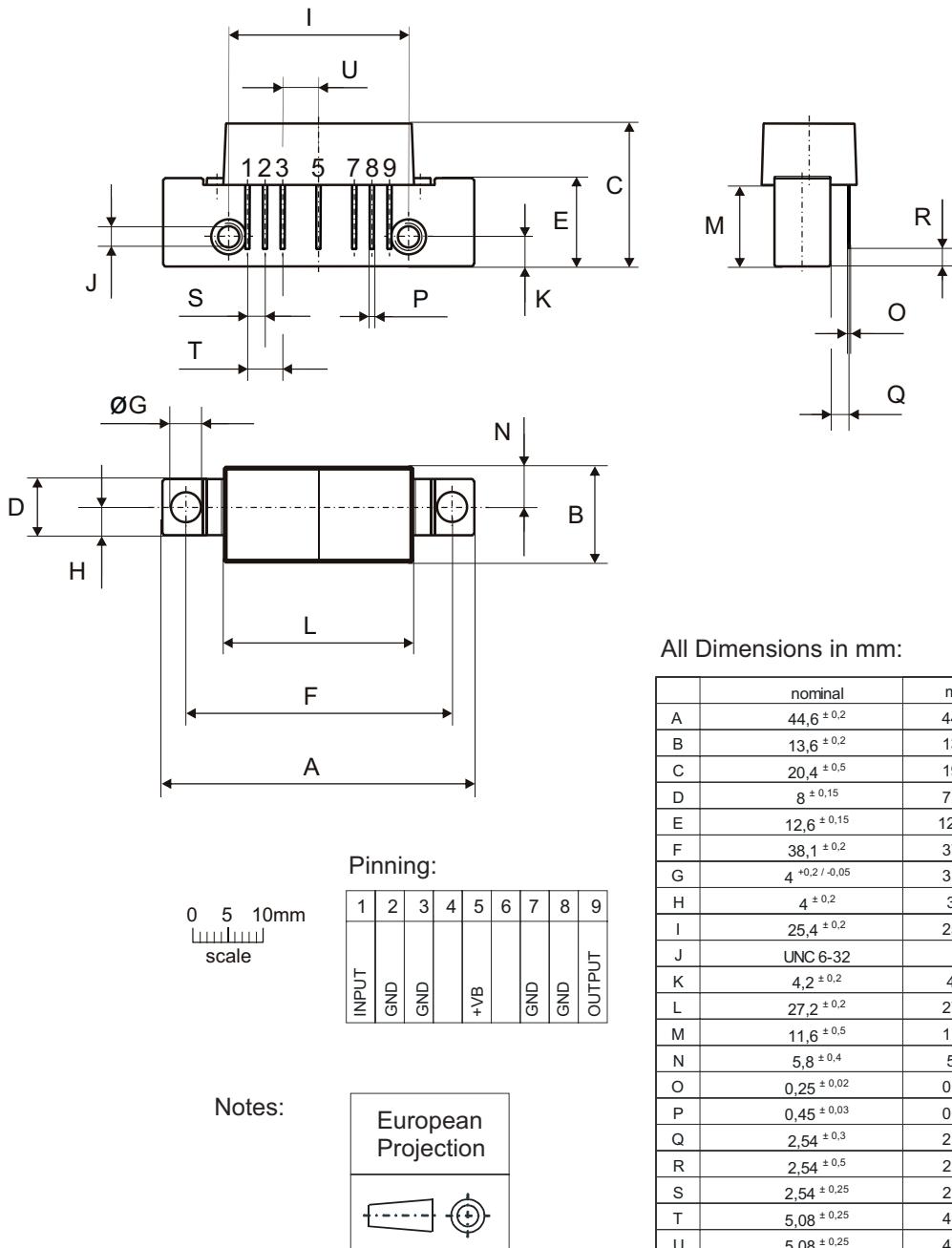
[1] The slope is defined as the difference between the gain at the start frequency and the gain at the stop frequency.

[2] 79 analog channels, NTSC frequency raster: 55.25MHz to 547.25MHz, +46dBmV flat output level, plus 75 digital channels, -6dB offset relative to the equivalent analog carrier.

[3] 112 analog channels, NTSC frequency raster: 55.25MHz to 745.25MHz, 44dBmV flat output level.

[4] Composite Second Order (CSO) - The CSO parameter (both sum and difference products) is defined by the NCTA.Composite Triple Beat (CTB) - The CTB parameter is defined by the NCTA.Cross Modulation (XMOD) - Cross modulation (XMOD) is measured at baseband (selective voltmeter method), referenced to 100% modulation of the carrier being tested.Carrier to Intermodulation Noise (CIN) - The CIN parameter is defined by ANSI/SCTE 17 (Test procedure for carrier to noise).

Package Drawing



All Dimensions in mm:

	nominal	min	max
A	44,6 ± 0,2	44,4	44,8
B	13,6 ± 0,2	13,4	13,8
C	20,4 ± 0,5	19,9	20,9
D	8 ± 0,15	7,85	8,15
E	12,6 ± 0,15	12,45	12,75
F	38,1 ± 0,2	37,9	38,3
G	4 +0,2 / -0,05	3,95	4,2
H	4 ± 0,2	3,8	4,2
I	25,4 ± 0,2	25,2	25,6
J	UNC 6-32	-	-
K	4,2 ± 0,2	4,0	4,4
L	27,2 ± 0,2	27,0	27,4
M	11,6 ± 0,5	11,1	12,1
N	5,8 ± 0,4	5,4	6,2
O	0,25 ± 0,02	0,23	0,27
P	0,45 ± 0,03	0,42	0,48
Q	2,54 ± 0,3	2,24	2,84
R	2,54 ± 0,5	2,04	3,04
S	2,54 ± 0,25	2,29	2,79
T	5,08 ± 0,25	4,83	5,33
U	5,08 ± 0,25	4,83	5,33